

2SK1803

Silicon N-Channel Power F-MOS FET

■ Features

- Avalanche capacity guaranteed: EAS > 60mJ
- $V_{GS} = \pm 30V$ guaranteed
- High-speed switching: $t_f = 80ns$
- No secondary breakdown

■ Applications

- Contactless relay
- Diving circuit for a solenoid
- Driving circuit for a motor
- Control equipment
- Switching power supply

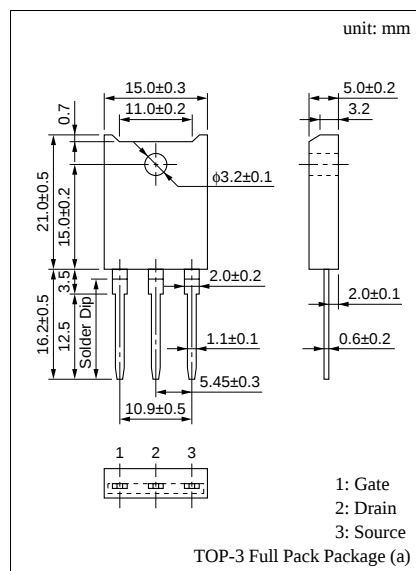
■ Absolute Maximum Ratings ($T_C = 25^\circ C$)

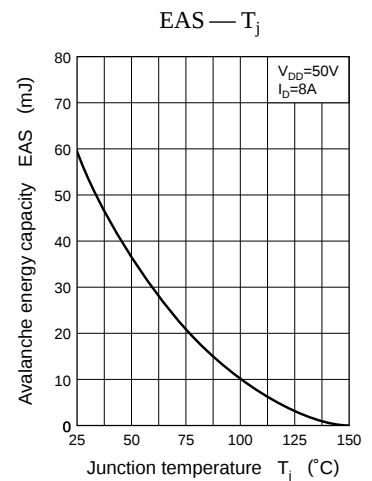
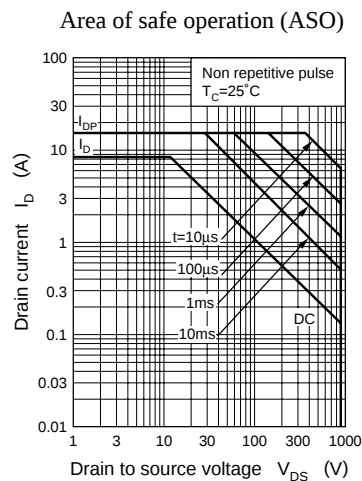
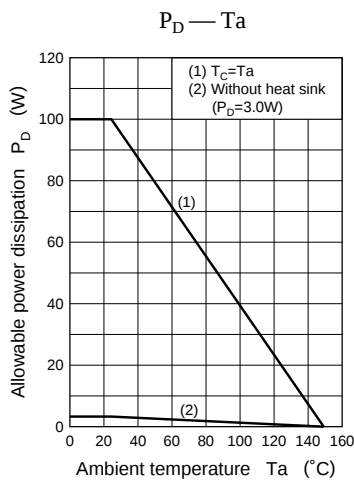
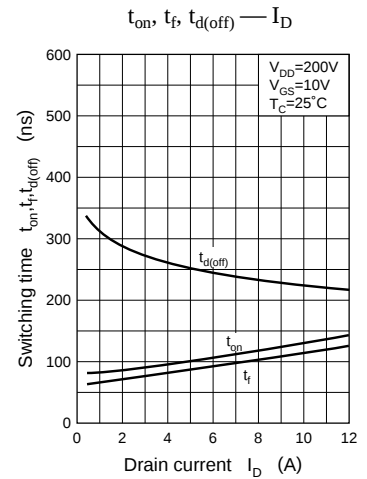
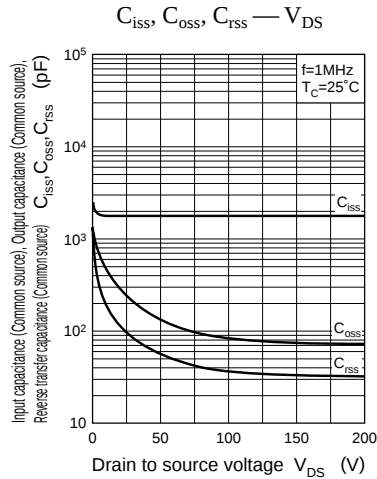
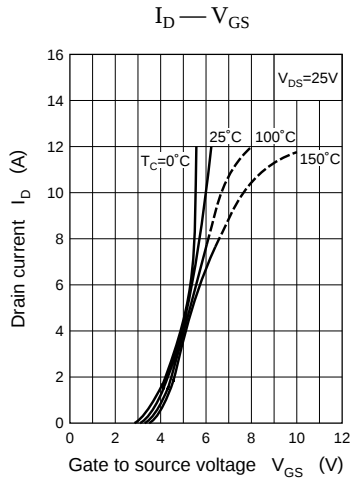
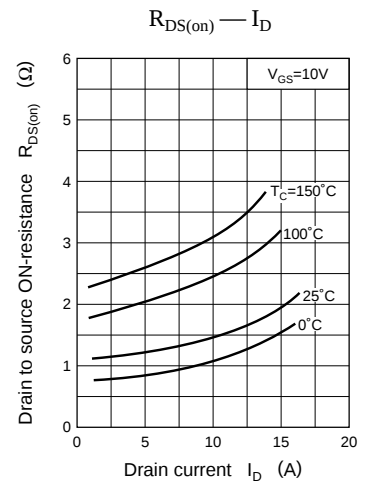
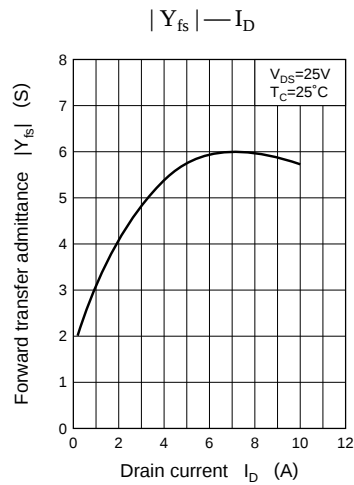
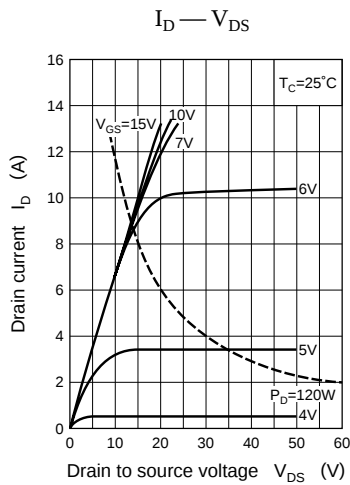
Parameter	Symbol	Ratings	Unit
Drain to Source breakdown voltage	V_{DSS}	900	V
Gate to Source voltage	V_{GSS}	± 30	V
Drain current	DC	I_D	A
	Pulse	I_{DP}	A
Avalanche energy capacity	EAS*	60	mJ
Allowable power dissipation	$T_C = 25^\circ C$	P_D	100
	$T_a = 25^\circ C$		3
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

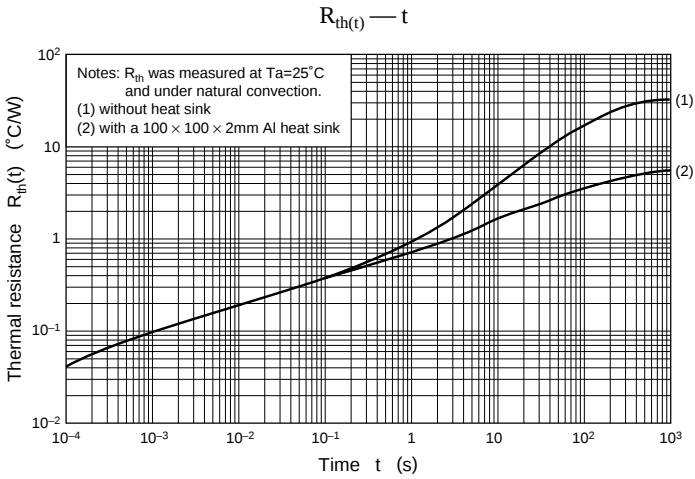
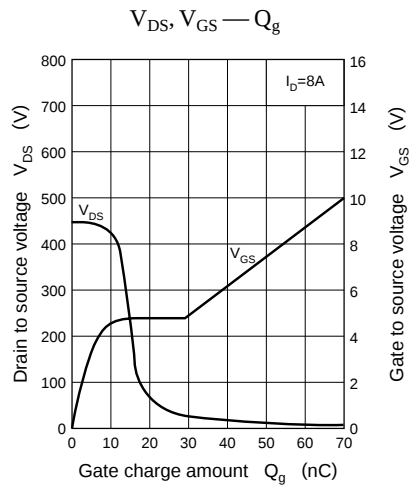
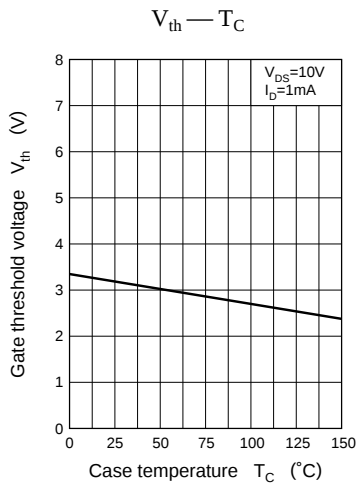
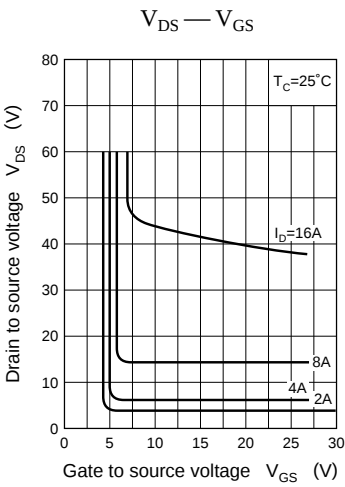
* $L = 1.9mH$, $I_L = 8A$, $V_{DD} = 50V$, 1 pulse

■ Electrical Characteristics ($T_C = 25^\circ C$)

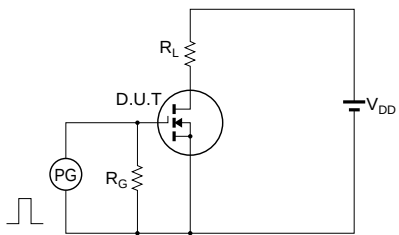
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I_{DSS}	$V_{DS} = 720V$, $V_{GS} = 0$			0.1	mA
Gate to Source leakage current	I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0$			± 1	μA
Drain to Source breakdown voltage	V_{DSS}	$I_D = 1mA$, $V_{GS} = 0$	900			V
Gate threshold voltage	V_{th}	$V_{DS} = 25V$, $I_D = 1mA$	1		5	V
Drain to Source ON-resistance	$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 4A$		1.3	1.7	Ω
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 25V$, $I_D = 4A$	3	5.5		S
Diode forward voltage	V_{DSF}	$I_{DR} = 8A$, $V_{GS} = 0$			-1.6	V
Input capacitance (Common Source)	C_{iss}	$V_{DS} = 20V$, $V_{GS} = 0$, $f = 1MHz$		1800		pF
Output capacitance (Common Source)	C_{oss}			200		pF
Reverse transfer capacitance (Common Source)	C_{rss}			90		pF
Turn-on time	t_{on}	$V_{GS} = 10V$, $I_D = 4A$ $V_{DD} = 200V$, $R_L = 50\Omega$		100		ns
Fall time	t_f			80		ns
Turn-off time (delay time)	$t_{d(off)}$			250		ns
Thermal resistance between channel and case	$R_{th(ch-c)}$				1.25	$^\circ C/W$







Switching measurement circuit



Avalanche energy capacity test circuit

